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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of

Applicant Yuanning Chen, et al.

Docket Number: TI-35022.2

Serial No.: 10/719,279

Art Unit: 2813

Filed: 11/21/03

Examiner: Jack S. J. Chen

For: Use of Hafnium Silicon Oxynitride as the Cap Layer of the
Sidewall Spacer

CERTIFICATION OF FACSIMILE TRANSMISSION

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FACSIMILE COVER SHEET

<input checked="" type="checkbox"/> FACSIMILE COVER SHEET	<input checked="" type="checkbox"/> AMENDMENT <u>116 (7 Pages)</u>
<input type="checkbox"/> NEW APPLICATION	<input checked="" type="checkbox"/> EOT <u>1 month</u>
<input type="checkbox"/> DECLARATION	<input type="checkbox"/> NOTICE OF APPEAL
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<input type="checkbox"/> CONTINUATION APP'N	<input type="checkbox"/> ELECTION
<input type="checkbox"/> DIVISIONAL APP'N	
NAME OF INVENTOR(S): Yuanning Chen, et al.	
RECEIPT DATE & SERIAL NO.: Serial No.: 10/719,279	
TITLE OF INVENTION: Use of Hafnium Silicon Oxynitride as the Cap Layer of the Sidewall Spacer Filing Date: 11/21/03	
TI FILE NO.: TI-35022.2	DEPOSIT ACCT. NO.: 20-0668
FAXED: 2-7-05 DUE: 12-18-04 ATTY/SECY: RAK/kjv	

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Examiner: Chen, Jack S J

Title: Use Of Hafnium Silicon Oxynitride As The Cap Layer Of The Sidewall
Spacer

AMENDMENT UNDER 37 C.F.R. §1.116

February 7, 2005

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Dear Commissioner:

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<u>Karen Vertz</u> Karen Vertz	<u>2-7-05</u> Date

In response to the Office Action, dated 10/18/2004, in the above-identified patent application, please make the following amendments. They are respectfully submitted as a full and complete response to that Action. Charge any required fees to the deposit account of Texas Instruments Incorporated, Account No. 20-0668.